

## N- and P-Channel 2.5-V (G-S) MOSFET

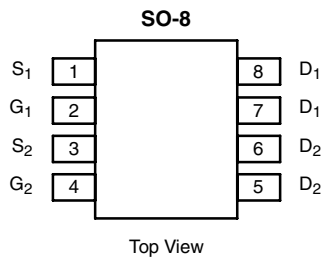
PRODUCT SUMMARY			
	V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
N-Channel	20	0.025 at V <sub>GS</sub> = 4.5 V	7.1
		0.035 at V <sub>GS</sub> = 2.5 V	6.0
P-Channel	- 20	0.033 at V <sub>GS</sub> = - 4.5 V	- 6.2
		0.050 at V <sub>GS</sub> = - 2.5 V	- 5.0

### FEATURES

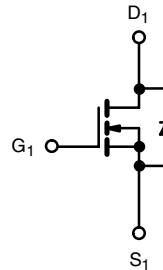
- TrenchFet<sup>®</sup> Power MOSFET: 2.5 Rated



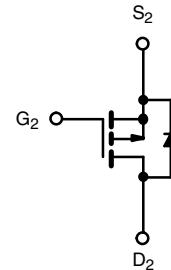
Available  
**RoHS\***  
COMPLIANT



Ordering Information: Si4562DY-T1  
Si4562DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	- 20	V
Gate-Source Voltage	V <sub>GS</sub>	± 12		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	7.1	- 6.2	A
	T <sub>A</sub> = 70 °C	5.7	- 4.9	
Pulsed Drain Current	I <sub>DM</sub>	40	- 40	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	1.7	- 1.7	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	2.0		W
	T <sub>A</sub> = 70 °C	1.3		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	N- or P-Channel	Unit
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	62.5	°C/W

Notes:

a. Surface Mounted on FR4 Board, t ≤ 10 sec.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

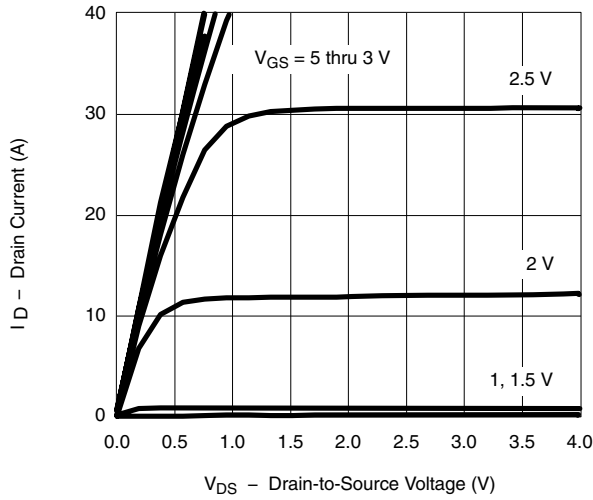
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
<b>Static</b>							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.6		1.6	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.6		-1.6	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$	N-Ch P-Ch			$\pm 100$ $\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			5	
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-5	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	N-Ch	20			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	P-Ch	-20			
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 7.1\text{ A}$	N-Ch		0.019	0.025	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -6.2\text{ A}$	P-Ch		0.027	0.033	
		$V_{GS} = 2.5\text{ V}, I_D = 6.0\text{ A}$	N-Ch		0.025	0.035	
		$V_{GS} = -2.5\text{ V}, I_D = -5.0\text{ A}$	P-Ch		0.040	0.050	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 7.1\text{ A}$	N-Ch		27		S
		$V_{DS} = -10\text{ V}, I_D = -6.2\text{ A}$	P-Ch		20		
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$	N-Ch			1.2	V
		$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$	P-Ch			-1.2	
<b>Dynamic<sup>b</sup></b>							
Total Gate Charge	$Q_g$	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 7.1\text{ A}$	N-Ch		25	50	nC
Gate-Source Charge	$Q_{gs}$		P-Ch		22	35	
Gate-Drain Charge	$Q_{gd}$	P-Channel $V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -6.2\text{ A}$	N-Ch		6.5		nC
			P-Ch		7		
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 6\text{ }\Omega$	N-Ch		40	60	ns
			P-Ch		27	50	
Rise Time	$t_r$	P-Channel $V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$	N-Ch		40	60	ns
Turn-Off Delay Time	$t_{d(off)}$		P-Ch		32	50	
Fall Time	$t_f$		N-Ch		90	150	ns
			P-Ch		95	150	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	N-Ch		40	80	ns
		$I_F = -1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	P-Ch		40	80	

## Notes:

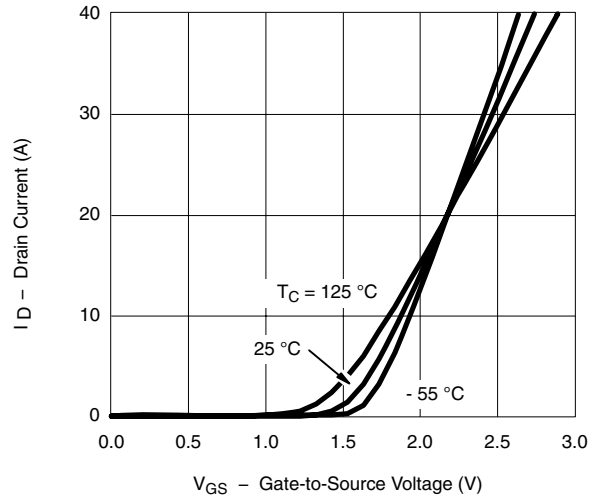
- a. For design aid only; not subject to production testing.  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

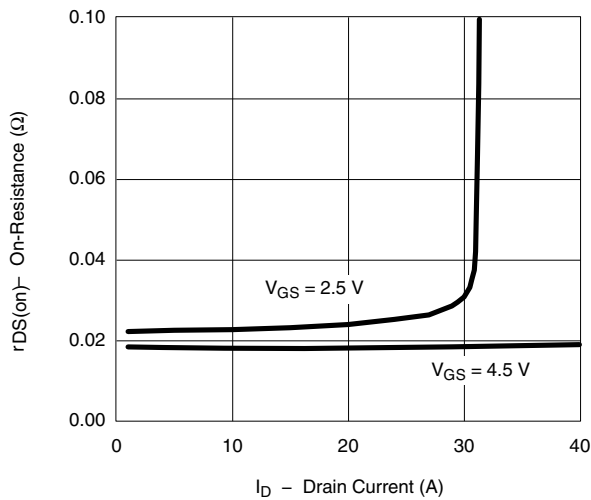
## N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



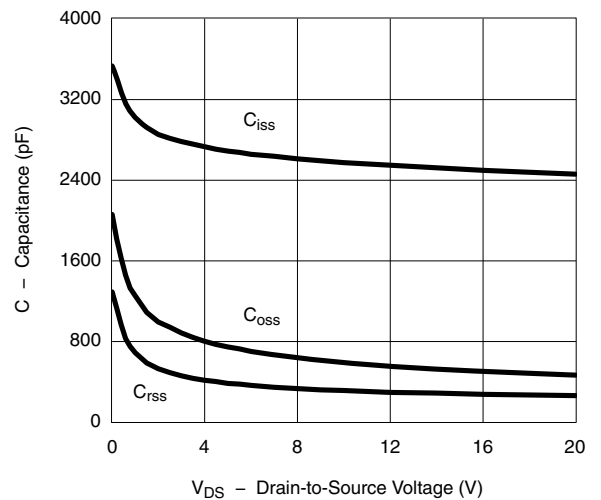
**Output Characteristics**



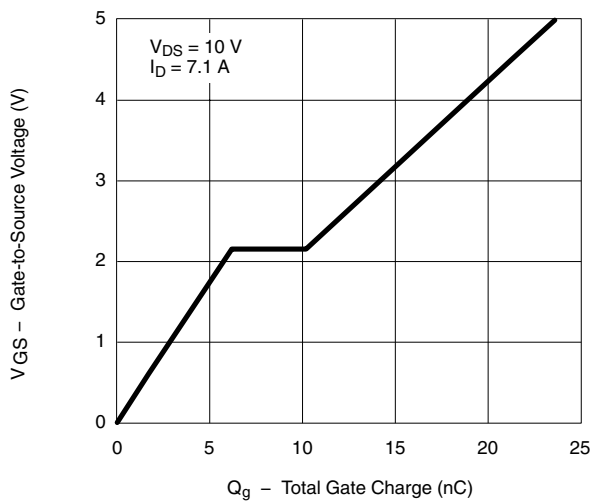
**Transfer Characteristics**



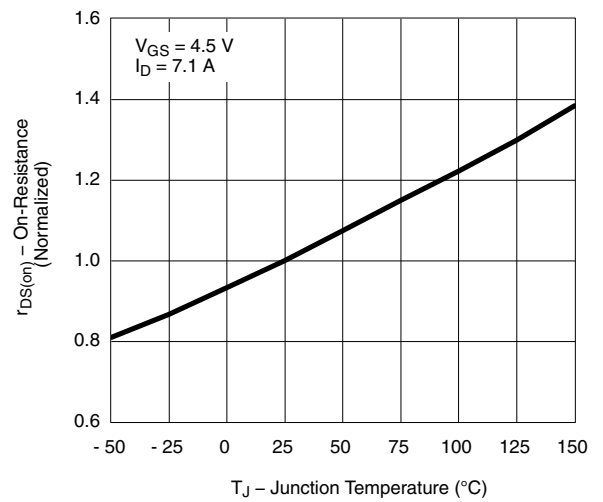
**On-Resistance vs. Drain Current**



**Capacitance**

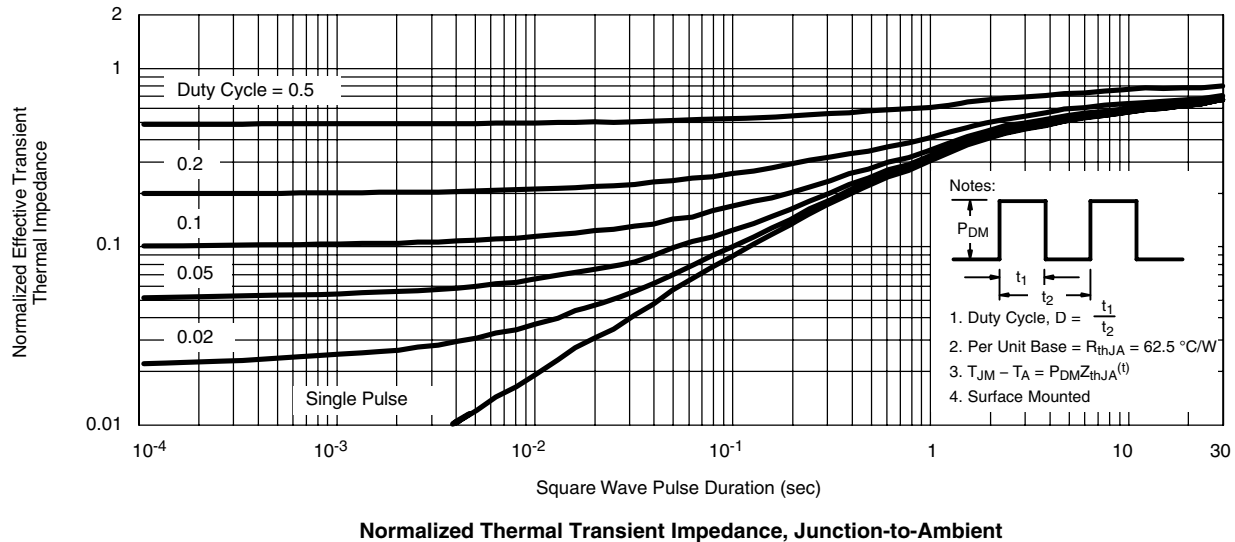
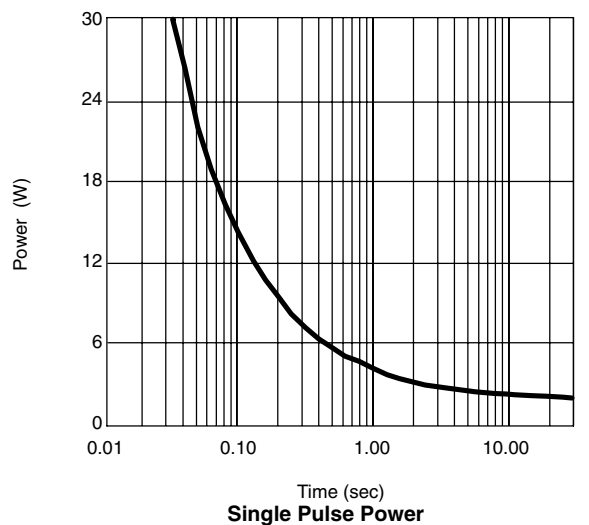
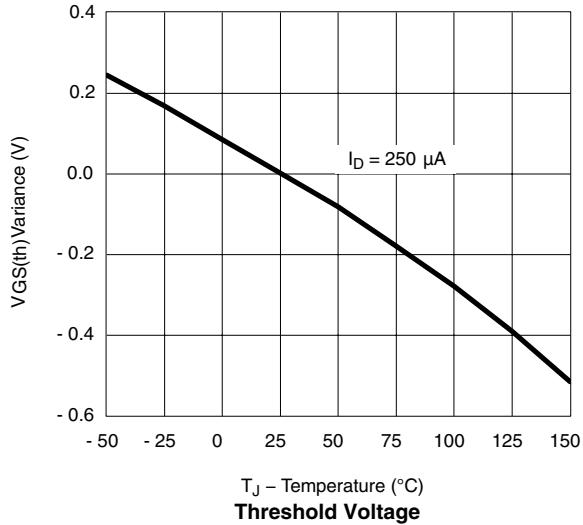
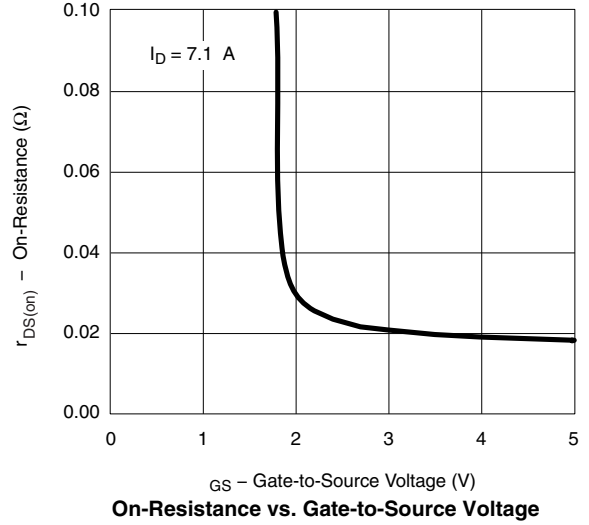
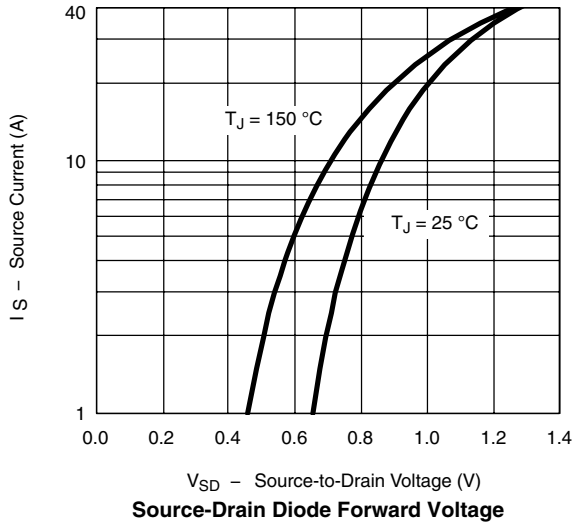


**Gate Charge**

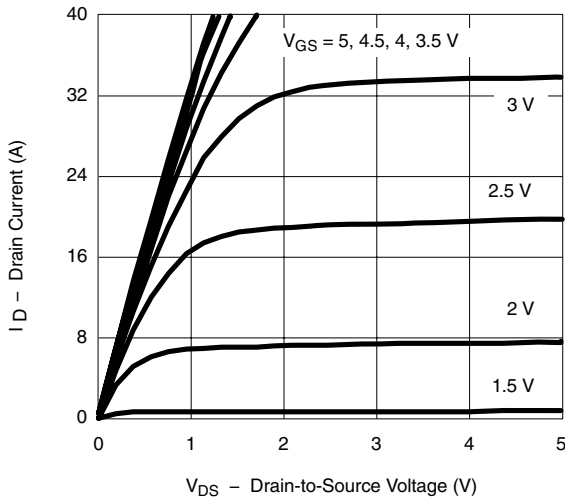


**On-Resistance vs. Junction Temperature**

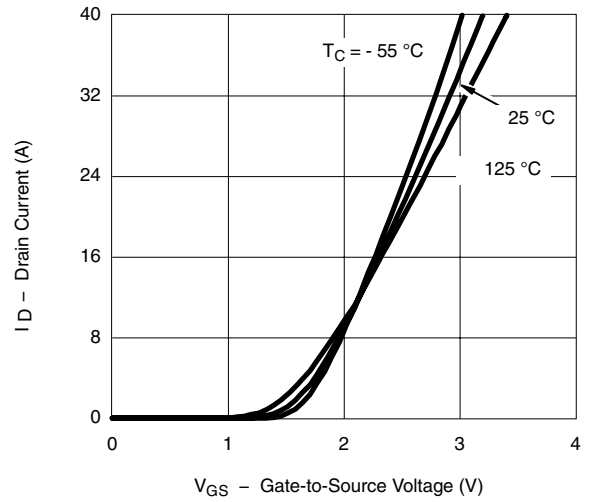
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless noted



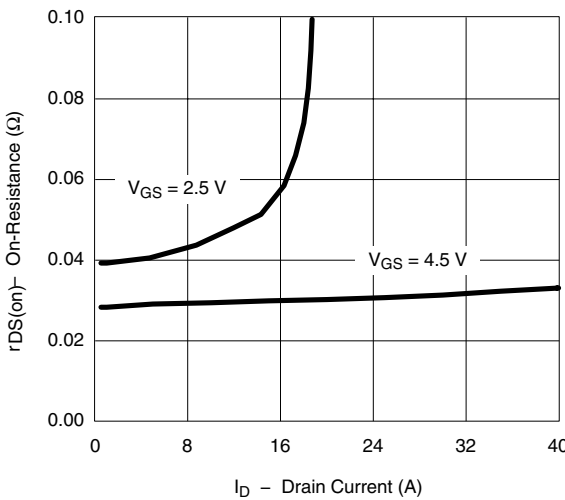
## P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



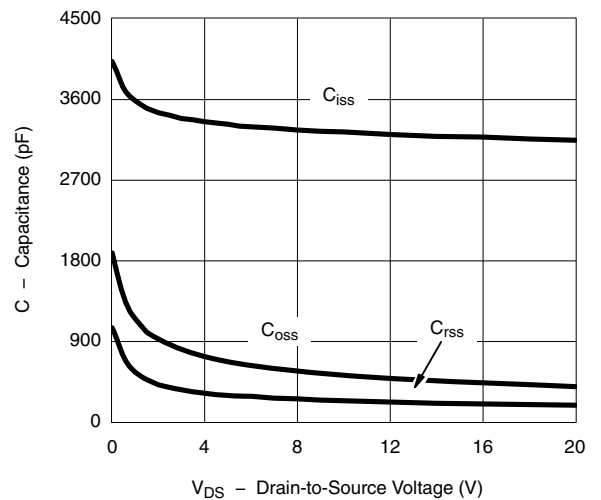
**Output Characteristics**



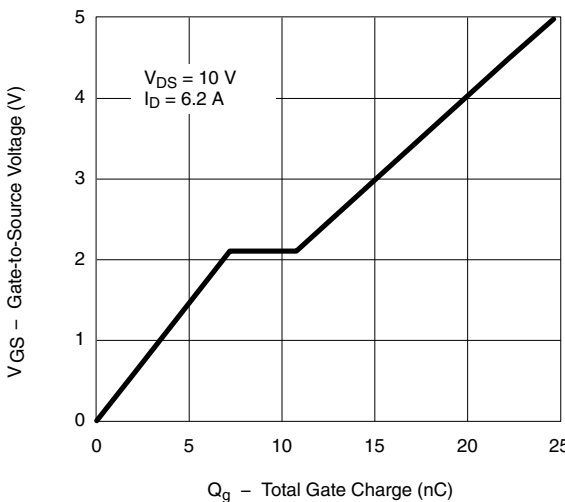
**Transfer Characteristics**



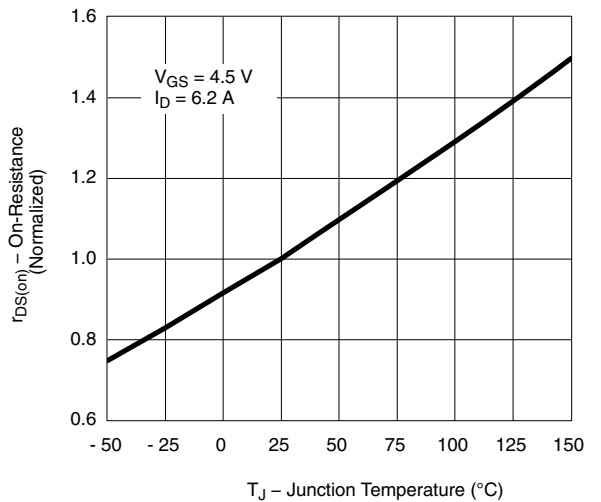
**On-Resistance vs. Drain Current**



**Capacitance**

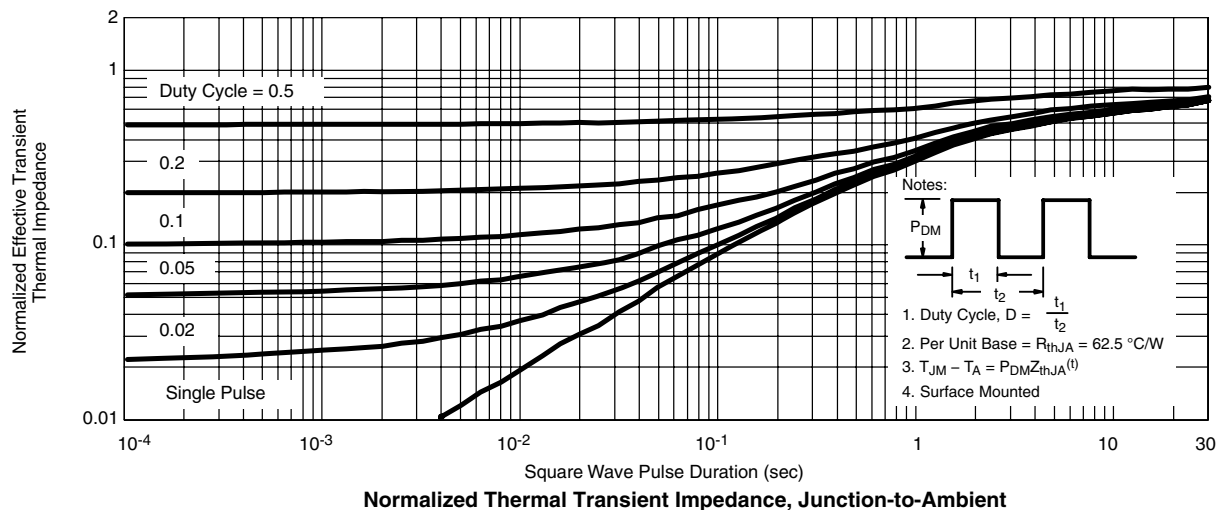
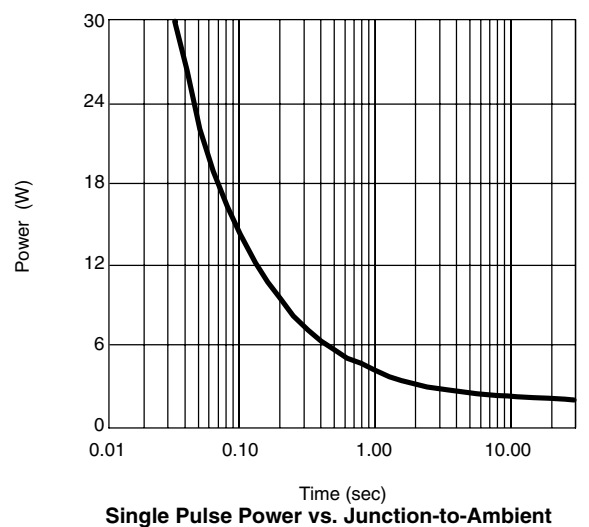
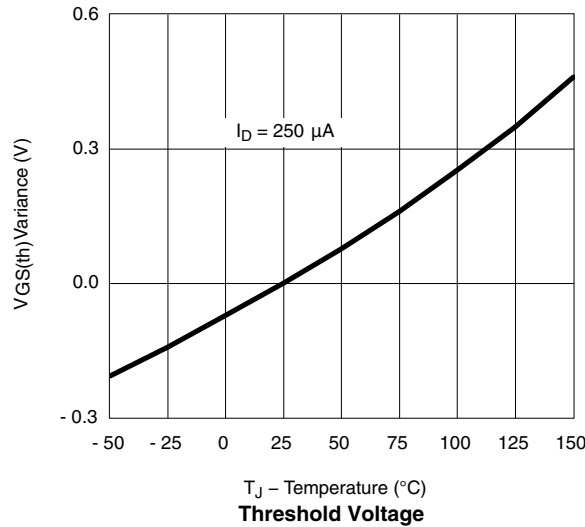
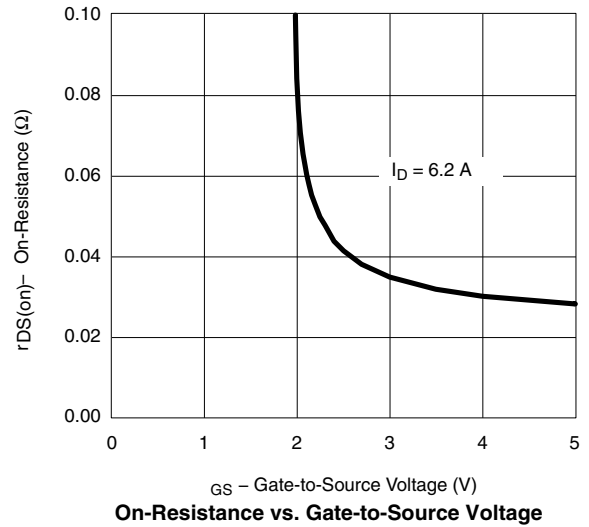
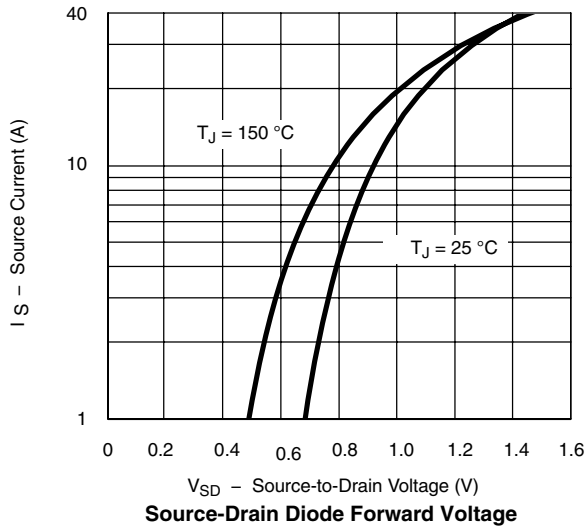


**Gate Charge**



**On-Resistance vs. Junction Temperature**

## P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



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